

Application Specific Discretes  $A.S.D.^{TM}$ 

## FIRE LIGHTER CIRCUIT

## FEATURES

- SPACE SAVING : MONOLITHIC FIRE LIGHTER FUNCTION INTEGRATION
- DEDICATED THYRISTOR STRUCTURE FOR CAPACITANCE DISCHARGE IGNITION OPERATION
- HIGH PULSE CURRENT CAPABILITY 150A @ tp = 10μs



## FUNCTIONAL DIAGRAM

#### DESCRIPTION

- The FLC02 is a high performance planar diffused technology adapted to high temperature and rugged environmental conditions.
- It has been developed especially for capacitance discharge operation. The main applications are ignitor circuits such as : fuel ignitiors / gas boilers...
- Th: Thyristor for switching operation.
- Z : Zener diode to set the threshold voltage.
- D : Diode for reverse conduction.
- R: 2 kOhm resistor.



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Symbol	Parameter	Value	Unit
ITRM	Repetitive surge peak on state current for thyristor	150	А
I <sub>FRM</sub>	Repetitive surge peak on state current for diode		
I <sub>TSM</sub>	Non repetitive surge peak on state current	5	А
di/dt	Critical rate of rise time on state current	120	A/μs
T <sub>stg</sub> Tj	Storage junction temperature range Maximum junction temperature	- 40 to + 150 + 125	°C
Toper	Operating temperature range	0 + 90	°C
TL	Maximum lead temperature for soldering during 10s	260	°C

## **ABSOLUTE RATINGS** (limiting values) : $0^{\circ}C < T_{amb} < 90^{\circ}C$

Note 1: Test current waveform



## THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th(j-a)</sub>	Thermal resistance junction to ambient	100	°C/W



## **ELECTRICAL CHARACTERISTICS**

Symbol	Parameters		
V <sub>RM</sub>	Stand-off voltage		
V <sub>BO</sub>	V <sub>BO</sub> Breakover voltage		
V <sub>T</sub> On-state voltage drop			
VF	Diode voltage drop		
I <sub>RM</sub>	Leakage current		
I <sub>BO</sub>	Breakover current		



## **DIODE (D) PARAMETER**

Symbol	Test Conditions				Value	Unit	
VF	I <sub>F</sub> = 2A	tp≤1 ms		Tj = 25℃	MAX	1.7	V

## THYRISTOR (Th) and ZENER (Z) PARAMETERS

Symbol	Test conditions				Unit
I <sub>RM</sub>	V <sub>RM</sub> = 200 V	Tj = 25°C	MAX	10	μΑ
		Tj = 120℃	MAX	100	μΑ
V <sub>BO</sub>	at I <sub>BO1</sub> Pin 3 (gate) open	Tj = 25℃	MAX	250	V
Іво 1	at V <sub>BO</sub> Pin 3 (gate) open	Tj = 25℃	MAX	0.5	mA
I <sub>BO</sub> 2	at $V_{BO}$ Pin 1 (cathode) and pin 3 (gate) in c/c	Tj = 25℃	MIN	40	mA
VT	$I_T = 2A$ tp $\leq 1ms$	Tj = 25°C	MAX	1.7	V

Fig.1 : Relative variation of breakover current (IBO) versus junction temperature



#### **BASIC APPLICATION**



The applications of the FLC02 using the capacitance discharge topology operate in 2 modes :

- Ignition mode : Transistor T is OFF - Blanking mode : Transistor T is ON

## 1) IGNITION MODE (Transistor TOFF)

#### PHASE 1:

The energy coming from the mains is stored into the capacitorC. For that, the AC voltage is rectified by the diode Ds.

#### PHASE 2 :

At the end of the phase 1, the voltage across the capacitor C reaches the avalanche threshold of the zener. Then a current flows through the gate of the thyristor Th which fires.

The firing of the thyristor causes an alternating current to flow through the capacitor C.

The positive parts of this current flow through C, Th and the primary of the HV transformer.

The negative parts of the current flow through C, D and the primary of the HV transformer.

#### **RS RESISTOR CALCULATION**

The Rs resistor allows, in addition with the capacitor C, to adjust the spark frequency and to limitate the current from the mains. Its value shall allow the thyristor Th to fire even in the worst case. In this borderline case the system must fire with the lower RMS mains voltage value while the breakdown voltage and current of the FLC are at the maximum.

The maximum Rs value is equal to :

$$Rsmax = \frac{(V_{AC} \min x \sqrt{2}) - V_{BO} \max}{I_{BO1} \max}$$





Fig 2. : Spark frequency versus Rs and C



The couple Rs/C can be chosen with the previous curve. Keep in mind the Rs maximum limit for which the system would not work when the AC

mains is minimum.

The next curve shows the behavior with Rs=15kOhms and C=1 $\mu$ F.



Fig. 3 : Voltage across the capacitance with Rs = 15 kOhms and C =  $1\mu$ F

#### PEAK CURRENT LIMIT

This component is designed to withstand Ip = 150A for a pulse duration of  $10\mu s$  for an ambient temperature of  $90^{\circ}C$ .

The curve of peak current versus the pulse duration allows us to verify if the application is within the FLC operating limit.



## POWER LOSSES (For 10µs, see note 1)

To evaluate the power losses, please use the following equations : For the thyristor :  $P = 1.18 \times I_{T(AV)} + 0.035 I_{T(RMS)}^2$ For the diode :  $P = 0.67 \times I_{F(AV)} + 0.106 I_{F(RMS)}^2$ 

## 2/ BLANKING MODE (Transistor Ton)

In this mode and transistor T is saturated and stops the spark generation.

In order to keep the thyristor Th in blanking mode and because of the power dissipation, the Resistor (Rs) has to keep a minimum value of 22 k $\Omega$  (see next curve) :



#### PACKAGE MECHANICAL DATA SOT82 (Plastic)



	DIMENSIONS				
REF.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	7.4	7.8	0.291	0.307	
В	10.5	10.8	0.413	0.425	
С	2.4	2.7	0.094	0.106	
D	0.7	0.9	0.027	0.035	
E	2.2 typ.		0.087 typ.		
F	0.49	0.75	0.019	0.029	
G	4.15	4.65	0.163	0.183	
H (1)		2.54		0.100	
L	15.7 typ.		0.618 typ.		
М	1.0	1.3	0.039 0.051		

(1) Within this region the cross-section of the leads is uncontrolled

Marking type number Weight : 0.72 g.

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